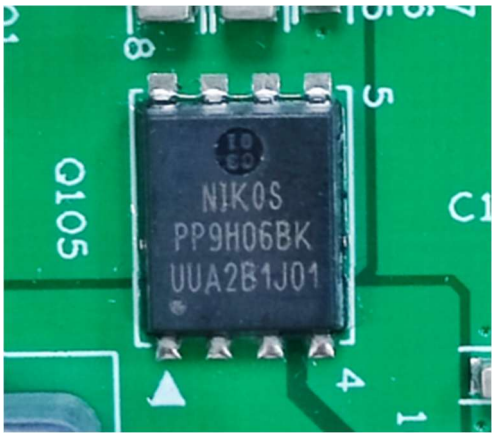

設計驗證
工程課
2025 -08- 20
發行
鈺瀧科技開發股份有限公司

Zenitron Corporation

增你強股份有限公司

台北市內湖區新湖二路250巷8號

TEL: (02)2792-8788 FAX: (02)2792-8909

業務承辦人員: 蘇芳儀 / Sarah Su EXT202

APPROVAL SHEET

公司名稱：鈺緯科技開發股份有限公司

零件種類：MOSFET

零件編號：3BPP9H0601Y (B0142)

客戶料號：PP9H06BK

零件包裝：PDFN 5x6P

製造廠商：NIKO SEM

設計驗證
工程課
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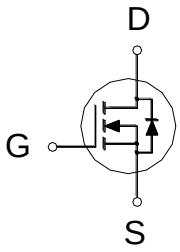
NIKO-SEM

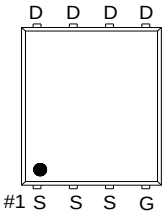
N-Channel Enhancement Mode Field Effect Transistor

PP9H06BK
PDFN 5x6P
Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
60V	9.1mΩ	60A





G. GATE
D. DRAIN
S. SOURCE

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	60	A
	T_C = 100 °C		42	
Pulsed Drain Current[1]		I_{DM}	80	
Continuous Drain Current	T_A = 25 °C	I_D	11.8	
	T_A = 70 °C		9.8	
Avalanche Current		I_{AS}	27	
Avalanche Energy	L = 0.1mH	E_{AS}	36	mJ
Power Dissipation	T_C = 25 °C	P_D	71	W
	T_C = 100 °C		35	
Power Dissipation[3]	T_A = 25 °C	P_D	2.7	W
	T_A = 70 °C		1.9	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	t ≦10s	$R_{\theta JA}$		55	°C / W
Junction-to-Ambient[2]	Steady-State	$R_{\theta JA}$		75	
Junction-to-Case	Steady-State	$R_{\theta JC}$		2.1	

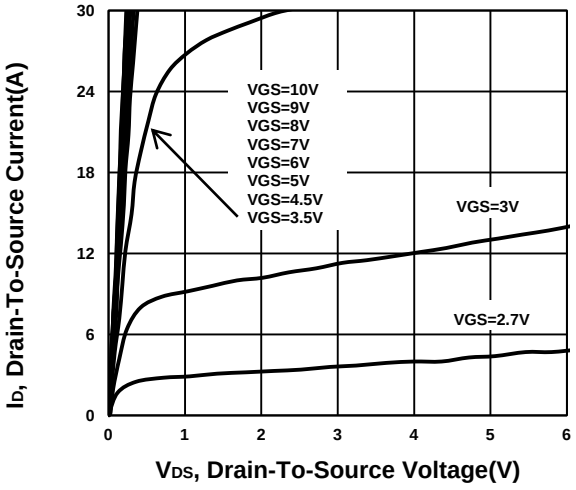
[1]Pulse width limited by maximum junction temperature.
[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
[3]The Power dissipation is based on $R_{\theta JA}$ t ≦10s value.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

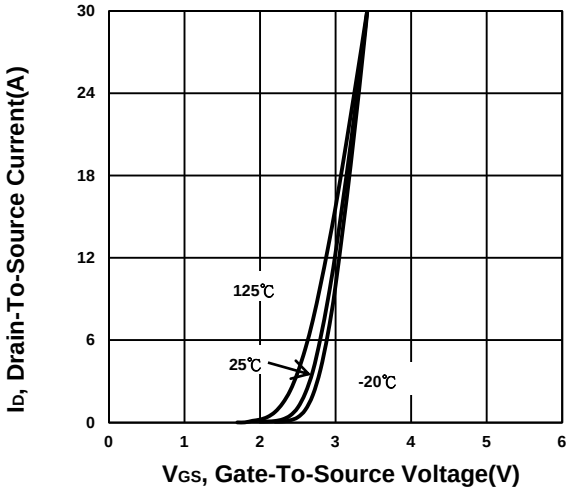
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS MIN	LIMITS TYP	LIMITS MAX	UNIT
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	1.8	3	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =60V, V_{GS} = 0V			1	μA
		V_{DS} = 60V, V_{GS} = 0V, T_J = 55 °C			10	μA
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 20A		7	9.1	mΩ
		V_{GS} = 4.5V, I_D = 20A		11.5	14.5	mΩ
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A		41		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 30V, f = 1MHz		1095		pF
Output Capacitance	C_{oss}			553		pF
Reverse Transfer Capacitance	C_{rss}			25		pF
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		0.9		Ω
Total Gate Charge[2]	Q_g VGS = 10V	V_{DS} = 30V , V_{GS} = 10V, I_D = 20A		18		nC
	Q_g V_{GS} = 4.5V			9.5		nC
Gate-Source Charge[2]	Q_{gs}			3		nC
Gate-Drain Charge[2]	Q_{gd}			4.5		nC
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 30V , I_D ≅ 20A, V_{GS} = 10V, R_{GEN} =6Ω		9.5		nS
Rise Time[2]	t_r			5.3		nS
Turn-Off Delay Time[2]	$t_{d(off)}$			24		nS
Fall Time[2]	t_f			28		nS
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				59	A
Forward Voltage[1]	V_{SD}	I_F = 20A, V_{GS} = 0V			1.2	V
Reverse Recovery Time	t_{rr}	I_F = 20A, dI_F/dt = 100A / μS		31		nS
Reverse Recovery Charge	Q_{rr}			20		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

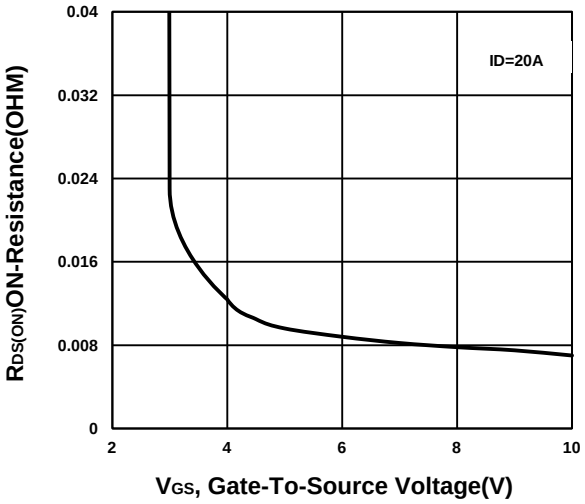
Output Characteristics



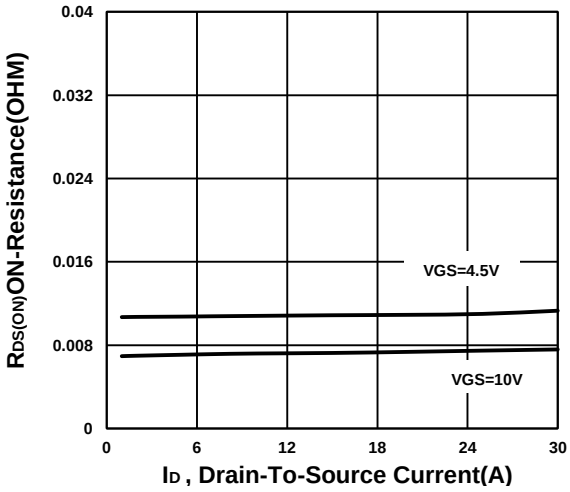
Transfer Characteristics



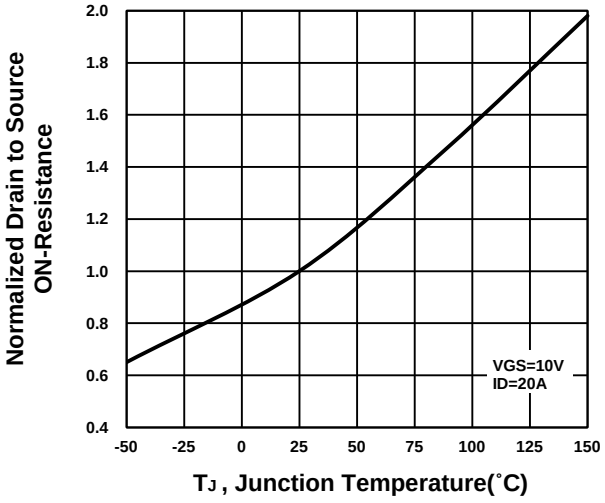
On-Resistance VS Gate-To-Source Voltage



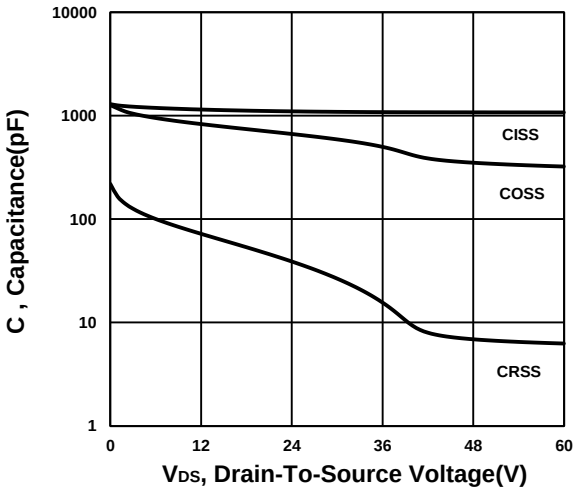
On-Resistance VS Drain Current



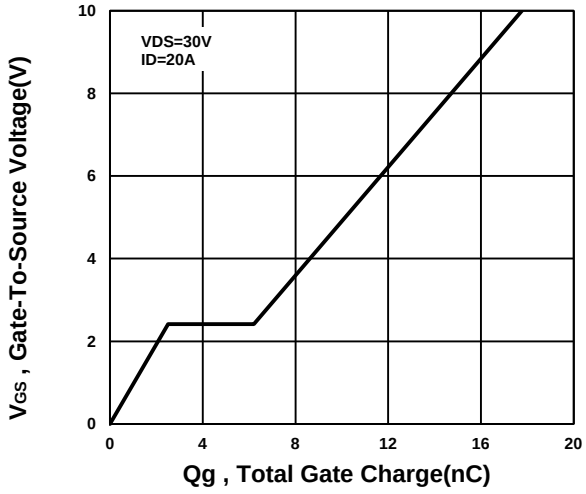
On-Resistance VS Temperature



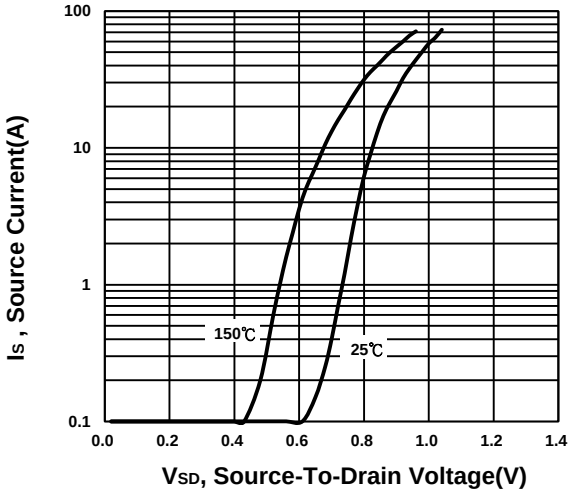
Capacitance Characteristic



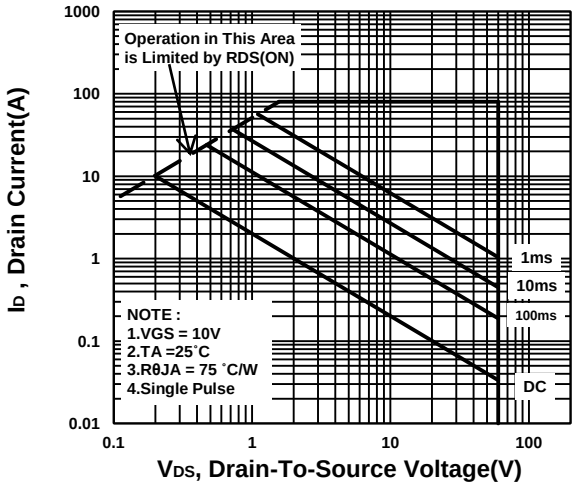
Gate charge Characteristics



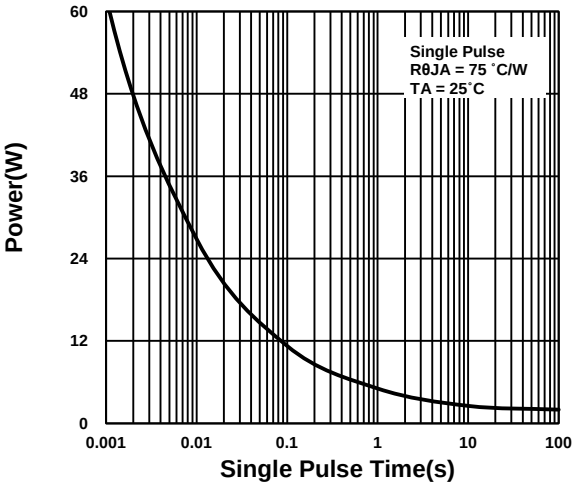
Source-Drain Diode Forward Voltage



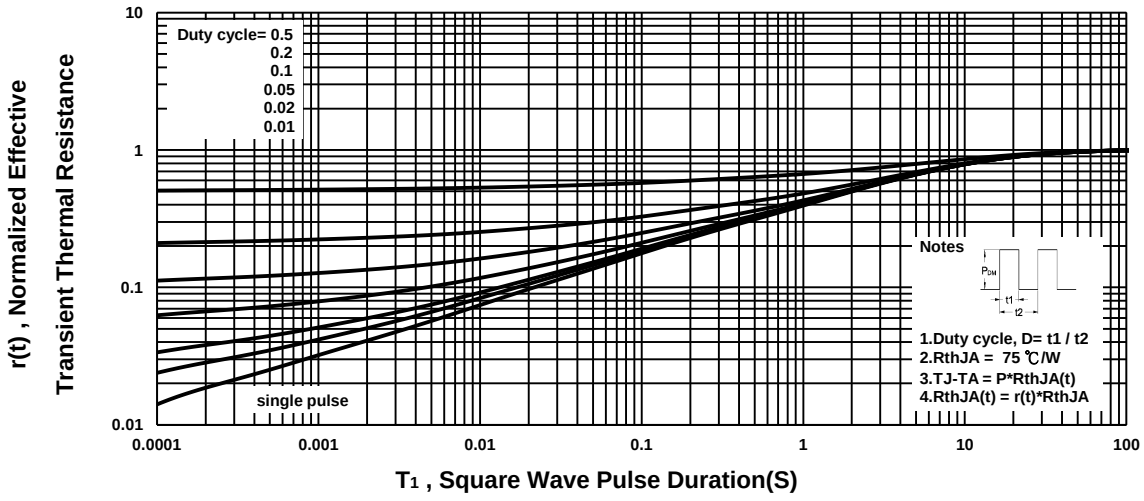
Safe Operating Area



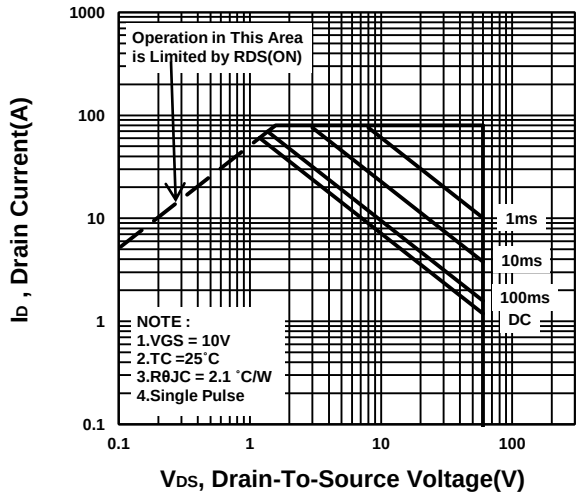
Single Pulse Maximum Power Dissipation



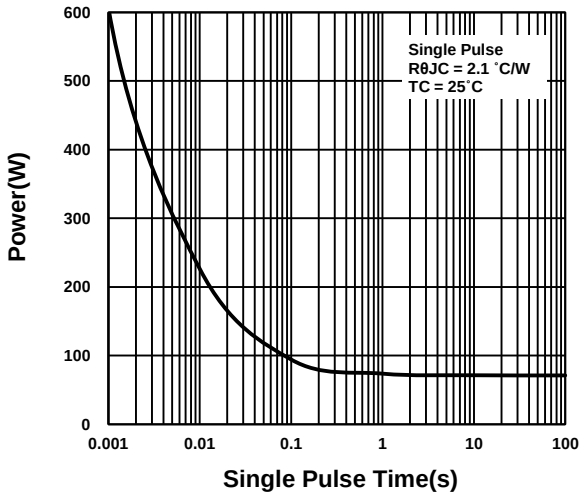
Transient Thermal Response Curve



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

